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09/964,484	09/28/2001	Toru Ishida	H-1013	2783	
7590 07/13/2005			EXAMINER		
Mattingly, Stanger & Malur, P.C.			WILLIAMS, ALEXANDER O		
Suite 370 1800 Diagonal Road			ART UNIT	PAPER NUMBER	
Alexandria, VA 22314			2826		
			DATE MAILED: 07/13/200:	5	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)		(m)		
Office Action Summary		09/964,484	ISHIDA ET AL.		9		
		Examiner	Art Unit		t		
		Alexander O. Williams	2826				
Period fo	The MAILING DATE of this communication apported to the communication apport.	pears on the cover sheet	with the correspondence addr	ess			
THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a repl period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by statute reply received by the Office later than three months after the mailined patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may y within the statutory minimum of will apply and will expire SIX (6) No. c, cause the application to become	a reply be timely filed thirty (30) days will be considered timely. ONTHS from the mailing date of this commandate of the commandate of	nunication	ı.		
Status							
1)⊠	Responsive to communication(s) filed on 19 A	pril 2005.	•				
· <u> </u>		action is non-final.					
3)□	·						
Disposit	ion of Claims						
5)□ 6)⊠ 7)□	 Claim(s) 1-31 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. Claim(s) is/are allowed. Claim(s) 1-31 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or election requirement. 						
Applicat	ion Papers						
9)[The specification is objected to by the Examine	er.					
10)[The drawing(s) filed on is/are: a) acc	epted or b) objected	to by the Examiner.				
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)[Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Ex	·	- ' '		l) .		
Priority (under 35 U.S.C. § 119						
a)	Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Burea See the attached detailed Office action for a list	s have been received. s have been received ir rity documents have be u (PCT Rule 17.2(a)).	Application No en received in this National St	age			
Attachmen	nt(s)	-8-					
_	ce of References Cited (PTO-892)	4) 🔲 Intervie	w Summary (PTO-413)				
3) 🔲 Infor	ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) er No(s)/Mail Date		lo(s)/Mail Date of Informal Patent Application (PTO-1	52)			

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Serial Number: 09/964484 Attorney's Docket #: H-1013

Filing Date: 9/28/01;

Applicant: Ishida et al.

Examiner: Alexander Williams

Applicant's Response, filed 4/19/05, has been acknowledged.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(f) or (g) prior art under 35 U.S.C. 103(a).

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Claims 11 to 31 are rejected under 35 U.S.C. 102(e) as being anticipated by Oka et al. (U.S. Patent # 6,441,495 B1).

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- 11. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip 2A having on one main surface thereof a first bonding pad 21 and a plurality of second bonding pads 21; a second semiconductor chip 2B having on one main surface thereof a plurality of third bonding pads 22 interconnected electrically, the second semiconductor chip being disposed on the one main surface of the first semiconductor chip; a first lead 10a,10b having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first semiconductor chip; a plurality of second leads 10a,10b each having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first semiconductor chip; a first bonding wire W for connecting the first bonding pad on the first semiconductor chip with the inner lead of the first lead; a plurality of second bonding wires W for connecting the plural second bonding pads on the first semiconductor chip with the inner lead portions of the plural second leads; a third bonding wire W for connecting one of the plural third bonding pads on the second semiconductor chip with the inner lead portion of the first lead; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portions of the first, second and third leads, and the first, second and third bonding wires.
- 12. A semiconductor device according to claim 11, Oka et al. show wherein the second semiconductor chip is formed in a quadrangular shape in plan, and wherein the plural third bonding pads are arranged along at least one side of the second semiconductor chip.
- 13. A semiconductor device according to claim 11, Oka et al. show wherein the second semiconductor chip is formed in a quadrangular shape in plan, and wherein the plural third bonding pads are arranged along at least two sides contiguous to each other of the second semiconductor chip.
- 14. A semiconductor device according to claim 11, Oka et al. show wherein the first bonding pad and the plural third bonding pads are bonding pads for signal.
- 15. A semiconductor device according to claim 11, Oka et al. show wherein the second semiconductor chip is formed in a plane size smaller than that of the first semiconductor chip.
- 16. A semiconductor device according to claim 11, Oka et al. ahow wherein another main surface of the second semiconductor chip opposed to the one main surface thereof is disposed on

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the one main surface of the first semiconductor chip so as to be facing the one main surface of the first semiconductor chip.

- 17. A semiconductor device according to claim 11, Oka et al. show wherein the first and third bonding wires are connected to one and same surface of the first lead.
- 18. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device B comprising: a first semiconductor chip 2A having on one main surface thereof a first bonding pad 21 and a second bonding pad 21 both disposed along one side of the one main surface; a second semiconductor chip 2B quadrangular in shape and having on one main surface thereof a third bonding pad 22 and two fourth bonding pads 22 interconnected electrically, the third and fourth bonding pads being disposed along one side of the one main surface of the second semiconductor chip, the third bonding pad being disposed between the fourth bonding pads, the second semiconductor chip being disposed on the one main surface of the first semiconductor chip in such a manner that the one side of the one main surface thereof is opposite to the one side of the one main surface of the first semiconductor chip; a first lead 10a, 10b and a second lead 10a,10b each having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed outside the one side of the first semiconductor chip; a first bonding wire W for connecting the first bonding pad on the first semiconductor chip with the inner lead portion of the first lead; a second bonding wire W for connecting the second bonding pad on the first semiconductor chip with the inner lead portion of the second lead; a third bonding wire W for connecting the third bonding pad on the second semiconductor chip with the inner lead portion of the first lead; a fourth bonding wire W for connecting one of the two fourth bonding pads on the second semiconductor chip with the inner lead portion of the second lead; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portions of the first and second leads, and the first, second, third and fourth bonding wires. 19. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip 2A which is quadrangular and which has a first bonding pad 21 on one side of one main surface thereof; a second semiconductor chip 2B which is quadrangular and which has a second bonding pad 22 on one side of one main surface thereof, the one side of the one main surface of the second semiconductor chip being disposed on the one main surface of the first semiconductor chip relate to so as to be facing the one side of the one main surface of the first semiconductor chip; a lead 10a, 10b having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed outside the one side of the first semiconductor chip; a first bonding wire W connecting the first bonding pad on the first semiconductor chip with the inner lead portion of the lead; a second bonding wire W for

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connecting the second bonding pad on the second semiconductor chip with the inner lead portion of the lead; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portion of the lead, and the first and second bonding wires, wherein the second semiconductor chip is disposed on the one main surface of the first semiconductor chip in a state such that a central point of the second semiconductor chip is displaced so as to be positioned on one side of the first semiconductor chip with respect to a central point of the first semiconductor chip.

- 20. A semiconductor device according to claim 19, Oka et al. show wherein the central point of the first semiconductor chip is a point of intersection of a first center line extending in the same direction as the one side of the first semiconductor chip and a second center line orthogonal to the first center line, and wherein the central point of the second semiconductor chip is a point of intersection of a first center line extending in the same direction as the one side of the second semiconductor chip and a second center line orthogonal to the first center line.
- 21. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip 2A which is quadrangular in plan and which has a first bonding pad 21 on a first side of one main surface thereof and a second bonding pad 21 on a second side of the one main surface contiguous to the first side; a second semiconductor chip 2B which is quadrangular in plan and which has a third bonding pad 22 on one side of one main surface thereof and a fourth bonding pad 22 on a second side of the one main surface contiguous to the first side; the second semiconductor chip being disposed on the one main surface of the first semiconductor chip in a state such that the first side of the one main surface thereof is opposed to the first side of the first semiconductor chip and the second side of the one main surface thereof is opposed to the second side of the first semiconductor chip; a first lead 10a,10b having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed outside the first side of the first semiconductor chip; a second lead 10a,10b having an inner lead portion and an outer lead potion integral with the inner lead portion, the inner lead portion being disposed outside the second side of the first semiconductor chip; a first bonding wire W for connecting the first bonding pad on the first semiconductor chip with the inner lead portion of the first lead; a second bonding wire W for connecting the first bonding pad on the second-semiconductor chip with the inner lead of the first lead; a third bonding wire W for connecting the second bonding pad on the first semiconductor chip with the inner lead of the second lead; a fourth bonding wire W for connecting the second bonding pad on the second semiconductor chip with the inner lead of the second lead; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portions of the first and second leads,

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and the first to fourth bonding wires, wherein the second semiconductor chip disposed on the one main surface of the first semiconductor chip in a state such that a central point thereof is displaced so as to be positioned on the first and second sides of the first semiconductor chip.

22. A semiconductor device according to claim 21, Oka et al. show wherein the central point of the first semiconductor chip is a point of intersection of a first center line extending in the same direction as the first side of the first semiconductor chip and a second center line orthogonal to the first center line, and wherein the central point of the second semiconductor chip is a point of intersection of a first center line extending in the same direction as the first side of the second semiconductor chip and a second center line orthogonal to the first center line.

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- 23. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip **2A** which is quadrangular and which has a first bonding pad **21** on one side of one main surface thereof; a second semiconductor chip **2B** which is quadrangular and which has a second bonding pad **22** on one side of one main surface thereof, the second semiconductor chip being disposed on the one main surface of the first semiconductor chip; a lead **10a,10b** having an inner lead and an outer lead integral with the inner lead, the inner lead being disposed outside the one side of the first semiconductor chip; a first bonding wire **W** for connecting the first bonding pad on the first semiconductor chip with the inner lead portion of the lead; a second bonding wire **W** for connecting the second bonding pad on the second semiconductor chip with the inner lead portion of the lead; and a resin seal member **4** for sealing the first and second semiconductor chips, the inner lead portion **10a,10b** of the lead, and the first and second bonding wires, wherein the second semiconductor chip is disposed on the first semiconductor chip in a state such that one side of the second semiconductor chip is opposed to two sides contiguous to each other of the first semiconductor chip so as to shorten the length of the second bonding wire.
- 24. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip **2A** having a first main surface and a second main surface opposed to each other, with a plurality of bonding pads **21** being formed on the first main surface; a second semiconductor chip **2B** having a first main surface and a second main surface opposed to each other, with a plurality of bonding pads **22** being formed on the first main surface, the second semiconductor chip being disposed on the first semiconductor chip in a state such that the second main surface thereof is opposed to the first main surface of the first semiconductor chip, the second semiconductor chip being smaller in plane size than the first semiconductor chip; a plurality of leads **10a,10b** each having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first

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semiconductor chip; a plurality of bonding wires W for connecting the plural bonding pads on the first and second semiconductor chips with the inner lead portions of the plural leads respectively; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portions of the plural leads, and the plural bonding wires, wherein the second semiconductor chip is smaller in thickness than the first semiconductor chip.

- 25. A semiconductor device according to claim 24, Oka et al. show wherein the second semiconductor chip is bonded to the first main surface of the first semiconductor chip through an adhesive layer (inherent).
- 26. A semiconductor device according to claim 25, Oka et al. show wherein the adhesive layer is formed by a bonding resin film.
- 27. A semiconductor device according to claim 25, Oka et al. show wherein the distance from the first main surface of the first semiconductor chip to the second main surface of the second semiconductor chip is smaller than the thickness of the first semiconductor chip.
- 28. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip 2A having a first main surface and a second main surface opposed to each other, with a plurality of bonding pads 21 being formed an the first main surface; a second semiconductor chip 2B having a first main surface and a second main surface opposed to each other, with a plurality of bonding pads 22 being formed on the first main surface, the second semiconductor chip being disposed on the first semiconductor chip in a state such that the second main surface thereof is opposed to the first main surface of the first semiconductor chip, the second semiconductor chip being smaller in plane size than the first semiconductor chip; a plurality of leads 10a,10b each having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first semiconductor chip; a plurality of bonding wires W for connecting the plural bonding pads on the first and second semiconductor chips with the inner lead portions of the plural leads respectively; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portions of plural leads, and the plural bonding wires, wherein the bonding pads on the second semiconductor chip are larger in plane size than the bonding pads on the first semiconductor chip.
- 29. Oka et al. (figures 1 to 30) specifically figure 7 show a semiconductor device **B** comprising: a first semiconductor chip **2A** having a first main surface and a second main surface opposed to each other, with a plurality of quadrangular bonding pads 21 being formed on the first main surface; a second semiconductor chip **2B** having a first main surface and a second main surface opposed to each other, with a plurality of quadrangular bonding pads **22** being formed on the

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first main surface, the second semiconductor chip being disposed on the first semiconductor chip in a state such that the second main surface thereof is opposed to the first main surface of the first semiconductor chip, the second semiconductor chip being smaller in plane size than the first semiconductor chip; a plurality of leads 10a,10b each having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first semiconductor chip; a plurality of first bonding wires **W** for connecting the plural bonding pads on the first semiconductor chip with the inner lead portions of the plural leads respectively; a plurality of second bonding wires **W** for connecting the plural bonding pads on the second semiconductor chip with the inner lead portions of the plural leads respectively; and a resin seal member 4 for sealing the first and second semiconductor chips, the inner lead portions of the plural. leads, and the first and second bonding wires, wherein the bonding pads on the second semiconductor chip are each formed in a rectangular shape wherein a side located in an extending direction of the bonding wires is longer than a side opposed to the leads.

- 30. A semiconductor device according to claim 29, Oka et al. show wherein the bonding pads on the second semiconductor chip are larger in plane size than the bonding pads on the first semiconductor chip.
- 31. A semiconductor device according to claim 29, Oka e tal. show wherein the second bonding wires each have a first portion extending in a direction perpendicular to the first main surface of the second semiconductor chip and a second portion extending along the first main surface of the second semiconductor chip, and wherein the first portion is positioned above the inner lead portions.

Claims 1 to 5 and 7 to 31 are Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Nishizawa et al. (U.S. Patent Application Publication # 2002/0030270 A1).

Claim 1 and similar claims 5, 11, 18, 19, 23, 24, 28 and 29, Nishizawa et al. (figures 1 to 27) specifically figures 5, 18 and 19 show a semiconductor device 1 comprising: a first semiconductor chip 20 having on one main surface thereof a control circuit, a first bonding pad, and a plurality of second bonding pads; a second semiconductor chip 30 having on one main surface thereof a memory circuit and a third bonding pad and disposed on the one main surface of the first semiconductor chip, the memory circuit being controlled in accordance with a control signal generated in the control circuit on the first semiconductor chip; a first lead 7 having an

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inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first semiconductor chip; a plurality of second leads 7 each having an inner lead portion and an outer lead portion integral with the inner lead portion, the inner lead portion being disposed at a position around the first semiconductor chip; a first bonding wire 8 for connecting the first bonding pad on the first semiconductor chip with the inner lead portion of the first lead; a plurality of second bonding wires 8 for connecting the plural second bonding pads on the first semiconductor chip with the inner lead portions of the plural second leads, a third bonding wire 8 for connecting the third bonding pad on the second semiconductor chip with the inner lead portion of the first lead; and a resin seal member 9 for sealing the first and second semiconductor chips, the first, second and third bonding wires, and the inner lead portions of the first and second leads. In claim 1 and similar claims 5, 11, 18, 19, 23, 24, 28 and 29, Nishizawa et al. show wherein the control signal generated in the control circuit is outputted from the first bonding pad on the first semiconductor chip and is inputted to the third bonding pad on the semiconductor chip through the first bonding wire, the first lead and the third bonding wire. Nishizawa et al. show the features of the claimed invention as detailed above, but fail to explicitly show the controller chip in on the bottom with the memory chip on the main surface of the controller chip. However, it would be obvious to one of ordinary skill in the art to reverse the order of the chips for the desired structure.

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- 2. A semiconductor device according to claim 1, Nishizawa et al.'s second semiconductor chip is formed in a plane size smaller than that of the first semiconductor chip.
- 3. A semiconductor device according to claim 1, Nishizawa et al. show an another main surface opposed of the second semiconductor chip opposed to the one main surface thereof is disposed on the one main surface of the first semiconductor chip in an opposed relation to the one main surface of the first semiconductor chip.
- 4. A semiconductor device according to claim 1, Nishizawa et al.'s first and third bonding wires are connected to one and same surface of the first lead.
- 7. A semiconductor device according to claim 5, Nishizawa et al.'s plural bonding pads on the first semiconductor chip include a first bonding pad, wherein the plural bonding pads on the second semiconductor chip include a second bonding pad, wherein the first bonding pad is electrically connected to an inner lead portion of one of the plural leads through a first bonding wire, wherein the second bonding pad is electrically connected to an inner lead portion of one of the plural leads through a second bonding wire, and wherein the serial data are outputted from the first bonding pad and inputted to the second bonding pad through the first bonding wire, one of the plural leads, and the second bonding wire.

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8. A semiconductor device according to claim 5, Nishizawa et al.'s second semiconductor chip is formed in a plane size smaller than that of the first semiconductor chip.

- 9. A semiconductor device according to claim 5, Nishizawa et al. show wherein another main surface of the second semiconductor chip opposed to the one main surface thereof is disposed on the one main surface of the first semiconductor chip in an opposed relation to the one main surface of the first semiconductor chip.
- 10. A semiconductor device according to claim 6, Nishizawa et al. show wherein the first and second bonding wires are connected to one and same surface of one of the plural leads.

Therefore, it would be obvious to one of ordinary skill in the art to use Nishizawa et al.'s teaching of the chips to use reverse order of the chips for the purpose of making it possible to develop and debug software.

Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over (U.S. Patent Application Publication # 2002/0030270 A1) in view of Ohie (U.S. Patent # 6,580,164 B1).

Nishizawa et al. show the features of the claimed invention as detailed above, but fail to explicitly show first semiconductor chip is a chip for a microcomputer, and wherein the second semiconductor chip is a chip for an EEPROM.

Ohie is cited for showing a first semiconductor chip is a chip for a microcomputer, and wherein the second semiconductor chip is a chip for an EEPROM for the purpose of making it possible to develop and debug software.

Therefore, it would be obvious to one of ordinary skill in the art to use Ohie's EEPROM as a semiconductor chip to modify Nishizawa et al.'s semiconductor chip for the purpose of making it possible to develop and debug software.

The listed references are cited as of interest to this application, but not applied at this time.

Response

Applicant's arguments filed 4/19/05 have been fully considered, but are moot in view of the new grounds of rejections detailed above.

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Field of Search	Date	
U.S. Class and subclass:	11/25/02	
257/723-25,728,777,784,786,666,676,685,686,692,	7/10/03	
696,698,796,777,684	3/4/04	
	10/15/04	
	7/9/05	
Other Documentation:	11/25/02	
foreign patents and literature in 257/723-	7/10/03	
25,728,777,784,786,666,676,685,686,692, 696,698,796,777,684	3/4/04	
	10/15/04	
	7/9/05	
Electronic data base(s):	11/25/02	
U.S. Patents EAST	7/10/03	
	3/4/04	
	10/15/04	
·	7/9/05	

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Alexander O Williams whose telephone number is (571) 272 1924. The examiner can normally be reached on M-F 6:30-7:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272 1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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AOW 7/9/05

Alexander Williams Primary Examiner